

Notice of References Cited

Application/Control No.

09/840,600

Applicant(s)/Patent Under
Reexamination
TSAI, ROGER S.

Examiner

Thien F Tran

Art Unit

2811

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Mahon et al., "A Technique for Modelling S-Parameters for HEMT Structures as a Function of Gate Bias", IEEE Transactions on Microwave Theory and Techniques, Vol. 40, No.7, July 1992, pp. 1430-1440.
	V	Hirose et al., "A Possible Scaling Limit for Enhancement-Mode GaAs MESFET's in DCFL Circuits", IEEE Transactions on Electron Devices, Vol. 39, No. 12, Dec. 1992, pp. 2681-2685.
	W	Schroter et al., "Investigation of Very Fast and High-Current Transients in Digital Bipolar IC's using Both a New Compact Model and a Device Simulator", IEEE Journal Of Solid-State Circuits, Vol. 30, No. 5, May 1995, pp. 551-562.
	X	Angelov et al., "A New Empirical Nonlinear Model for HEMT and MESFET Devices", IEEE Transactions on Microwave Theory and Techniques, Vol. 40, No.12, Dec. 1992, pp. 2258-2266.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.